

Presenting Author: Todd C. MacLeod  
Affiliation: NASA Marshall Space Flight Center  
Mailing Address: Todd C. MacLeod  
NASA Marshall Space Flight Center  
ES63  
Huntsville AL 35812  
Phone: 256-961-7716  
Fax: 256-961-7149  
Email: [todd.macleod@nasa.gov](mailto:todd.macleod@nasa.gov)

Paper Title: **Satellite Test of Radiation Impact on Ramtron 512K  
FRAM**  
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## Satellite Test of Radiation Impact on Ramtron 512K FRAM

Todd C. MacLeod  
NASA Marshall Space Flight Center

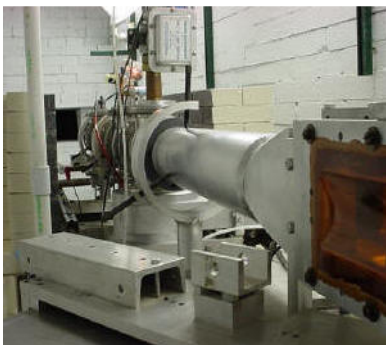
Rana Sayyah  
University of Alabama Huntsville

W. Herb Sims  
NASA Marshall Space Flight Center

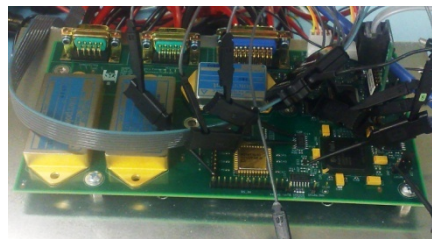
Kosta A. Varnavas  
NASA Marshall Space Flight Center

Fat D. Ho  
University of Alabama Huntsville

**Abstract:** The Memory Test Experiment is a space test of a ferroelectric memory device on a low Earth orbit satellite. The test consists of writing and reading data with a ferroelectric based memory device. Any errors are detected and are stored on board the satellite. The data is sent to the ground through telemetry once a day. Analysis of the data can determine the kind of error that was found and will lead to a better understanding of the effects of space radiation on memory systems. The test will be one of the first flight demonstrations of ferroelectric memory in a near polar orbit which allows testing in a varied radiation environment. The memory devices being tested is a Ramtron Inc. 512K memory device. This paper details the goals and purpose of this experiment as well as the development process. The process for analyzing the data to gain the maximum understanding of the performance of the ferroelectric memory device is detailed.



Radiation Testing of the MTE  
at Indiana University



Telemetry Board with the  
Memory Test Experiment